

# Microcalorimeters for X-ray Detection

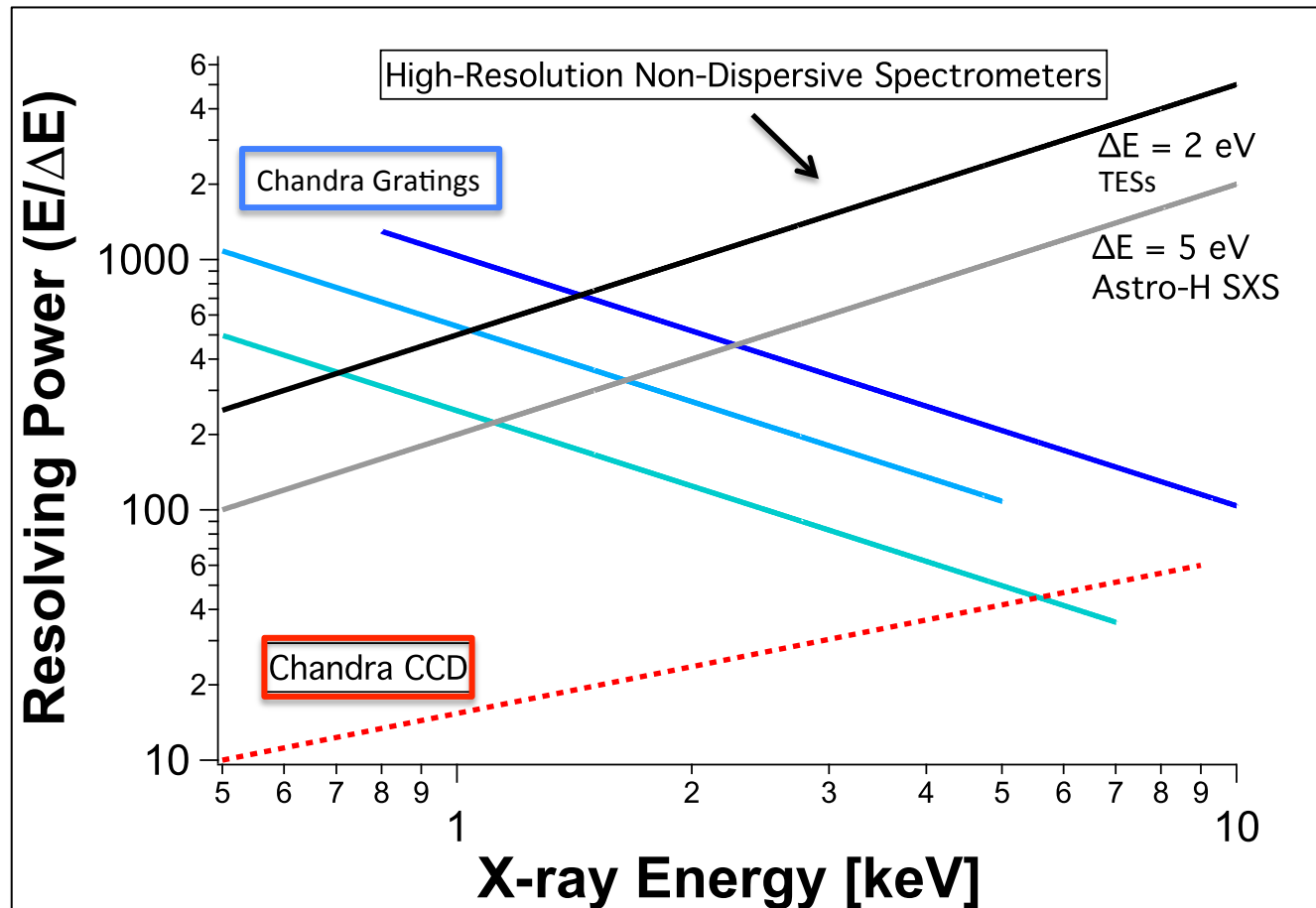
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Plus close collaboration with U. Wisconsin, Stanford/SLAC, NIST/Boulder, Northwestern, Yale

# Power of X-ray Microcalorimeters



## Non-Dispersive Imaging Spectroscopy !

- high resolving power at diagnostically rich 6 keV (Fe K-shell)
- spectroscopy of extended sources
- unity QE and photon counting

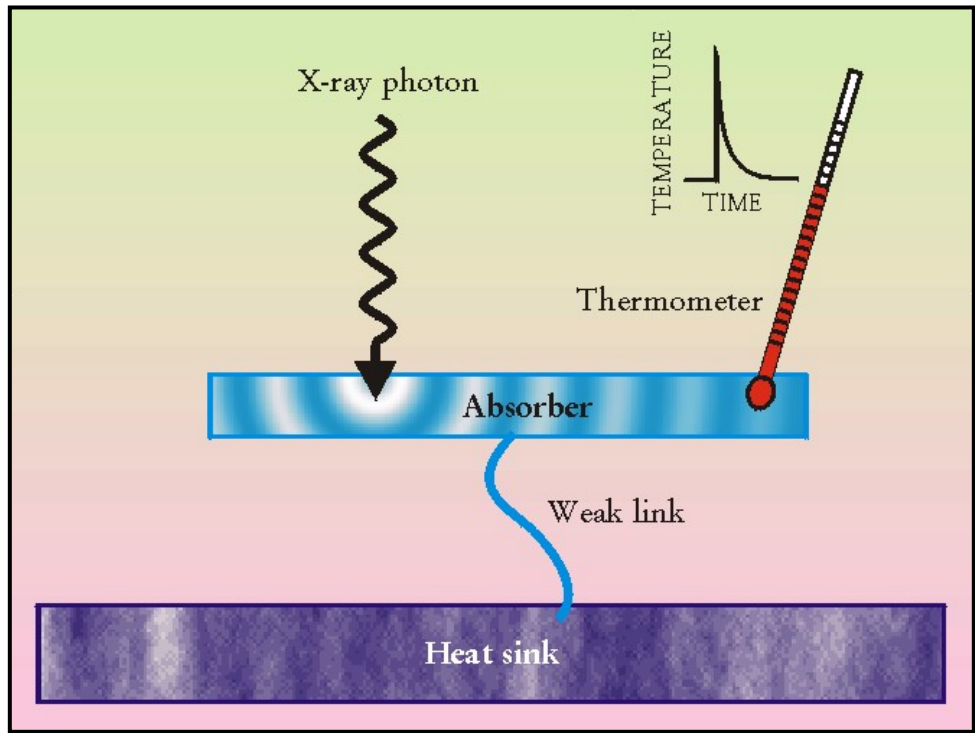
# Outline

- Intro to our X-ray microcalorimeters & sensors
- Two technical challenges
- Reduced heat capacity devices

note:  $\Delta E_{\text{FWHM}} = 2.355 \sigma$

# X-ray Microcalorimeter Concept

Non-dispersive spectrometer



## Thermal detection of individual X-ray photons

- High spectral resolution
- High intrinsic quantum efficiency

Signal:  $\delta T \propto \frac{E}{C_{tot}}$

Decay:  $\tau \propto \frac{C_{tot}}{G}$

Energy resolution is limited by thermodynamics:

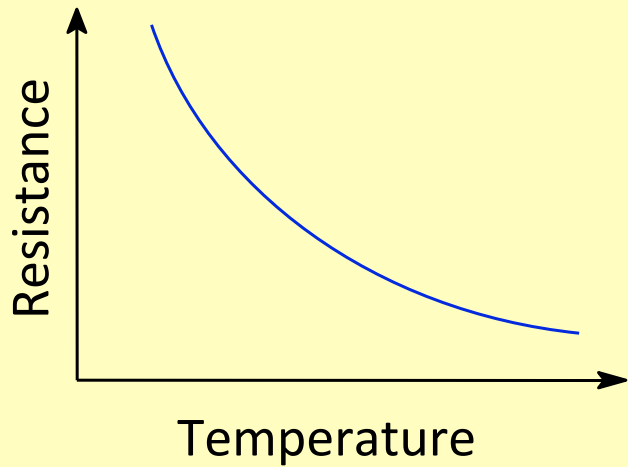
$$\Delta E \propto T C(T)^{0.5}$$

Operate at cryogenic temperatures (~50 mK)

$C_{tot}$  = total heat capacity  
 $G$  = thermal conductance

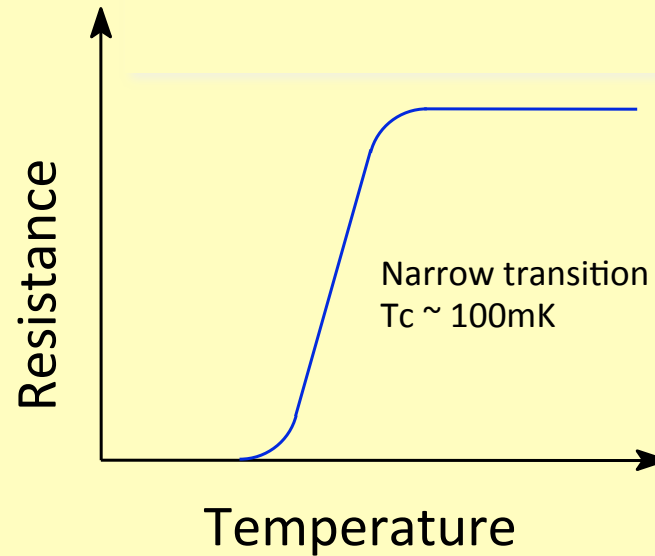
Several sensor approaches:

Semiconductor Thermometer  
(Doped Ge or Si)



Approach used for:  
XQC Sounding Rocket  
Astro-H Soft X-ray Spectrometer (SXS)

Superconducting Transition Edge  
Sensor (TES) Thermometer

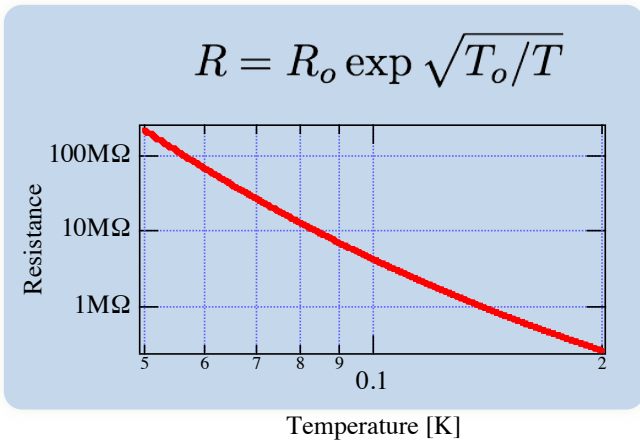


Large Arrays, Best E/ $\Delta E$

Also, magnetic calorimeters.

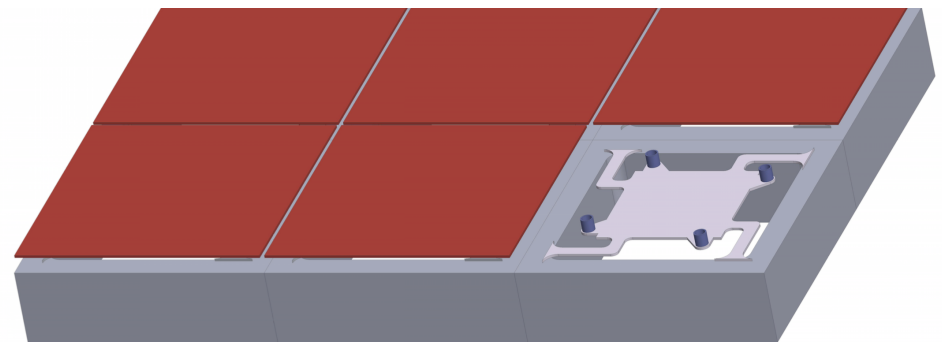
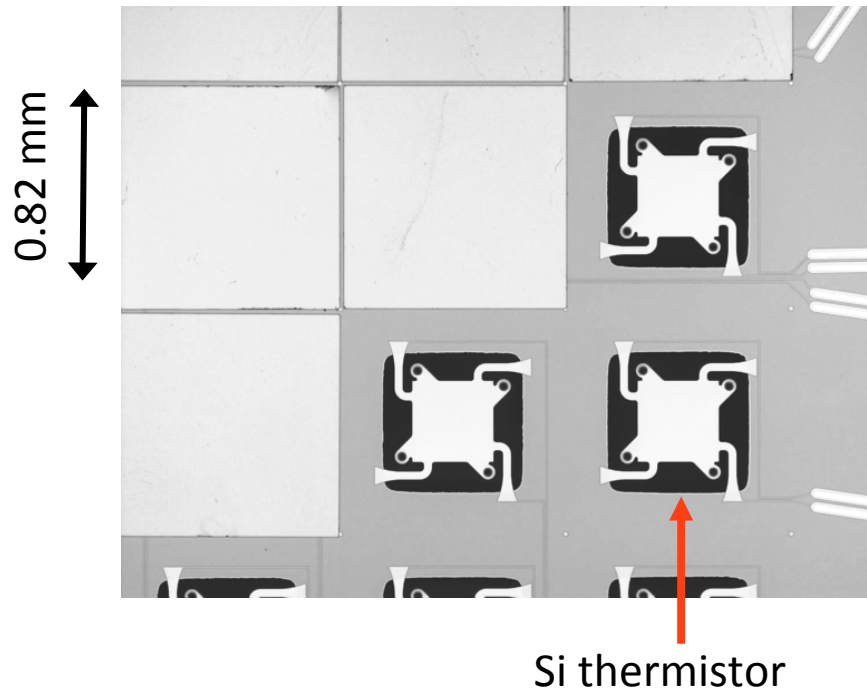
# Semiconductor Thermistors

- Ion-implanted Si  
(or Neutron Transmutation Doped Ge)
- High resistance,  
read out with JFET



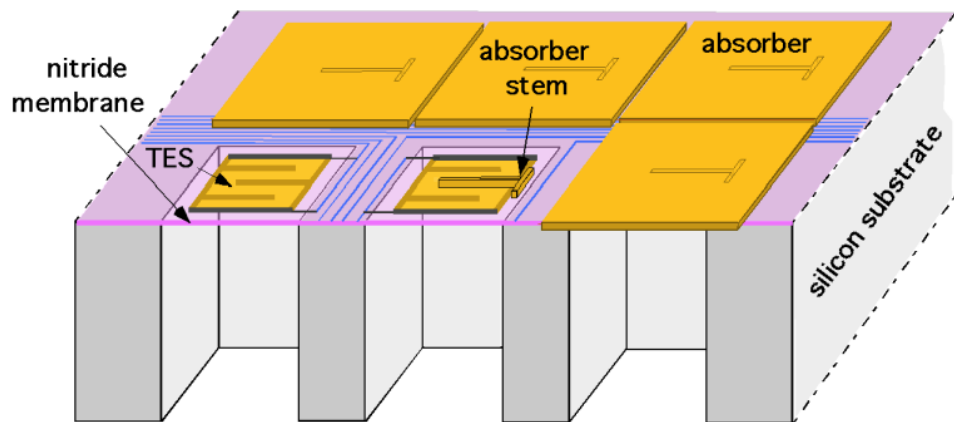
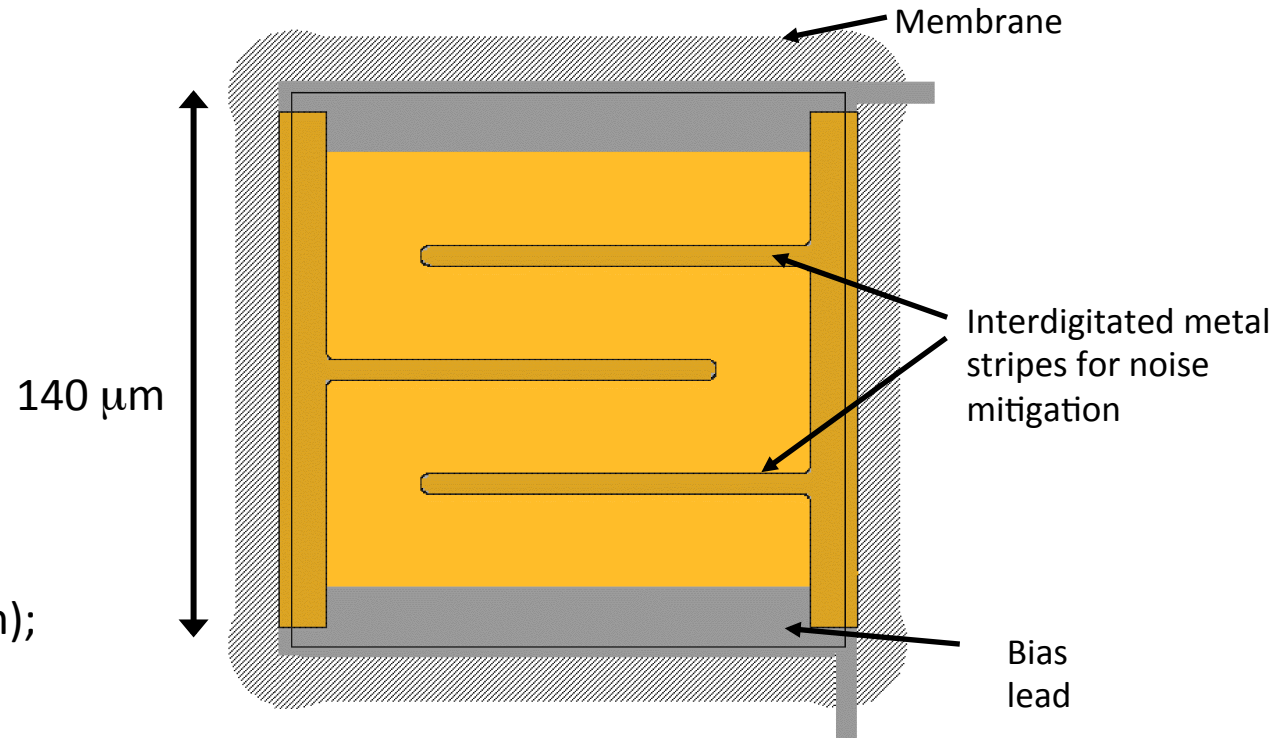
$\Delta E_{FWHM} \sim 4 \text{ eV}$  ( $R \sim 1500$  at 6 keV)

arrays of  $\sim 36$  pixels



## Mo/Au bilayer TES

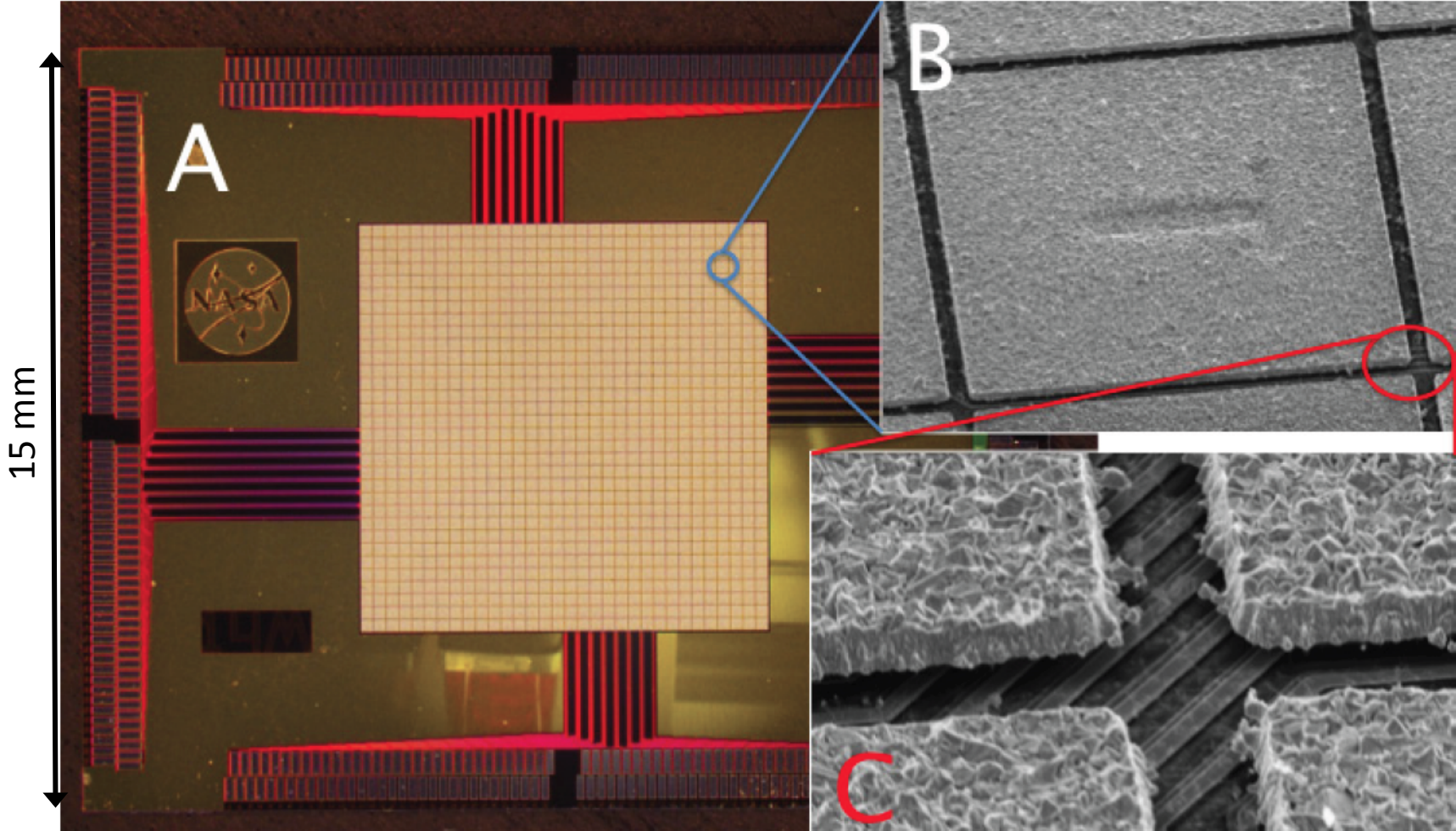
Mo (45 nm) / Au (225 nm);  
 $T_c = 0.1$  K



microcalorimeter array  
(0.1 – 12 keV,  $\Delta E_{FWHM} \sim 2$  eV)

- Si removed beneath pixels to leave TES sitting on SiN membrane
- overhanging absorbers are several microns thick (made of Au or Au/Bi), to provide high QE and appropriate C; even thicker absorbers used for high-energy x-ray or gamma-ray detectors

Recent TES X-ray Microcalorimeter Array Development:





## Energy Resolution and Device Optimization

$$\Delta E \propto T (C/\alpha)^{0.5} \quad \alpha = \frac{\partial \ln(R)}{\partial \ln(T)} \quad \beta = \frac{\partial \ln(R)}{\partial \ln(I)}$$

- $\Delta E$  is independent of  $E$  in small temperature excursion around  $T_c$
- Optimize detector design for best resolution with a certain  $E_{max}$ 
  - make heat capacity as small as possible and  $\alpha$  as high as possible without saturating detector, taking into account noise scaling

$$\Delta E \propto (T E_{max})^{0.5} \quad E_{max} \propto C T/\alpha$$

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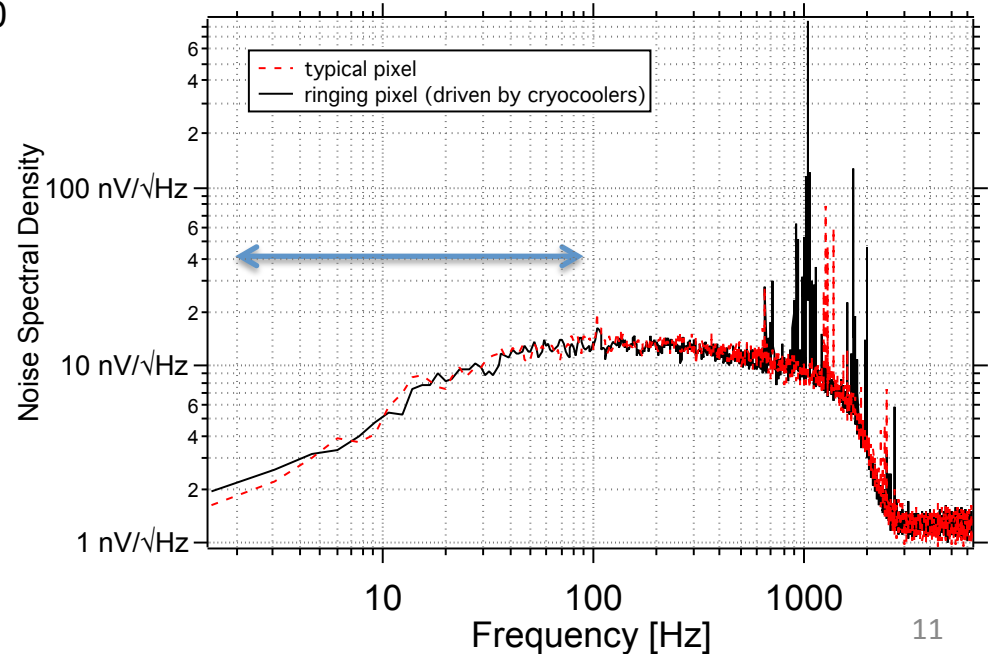
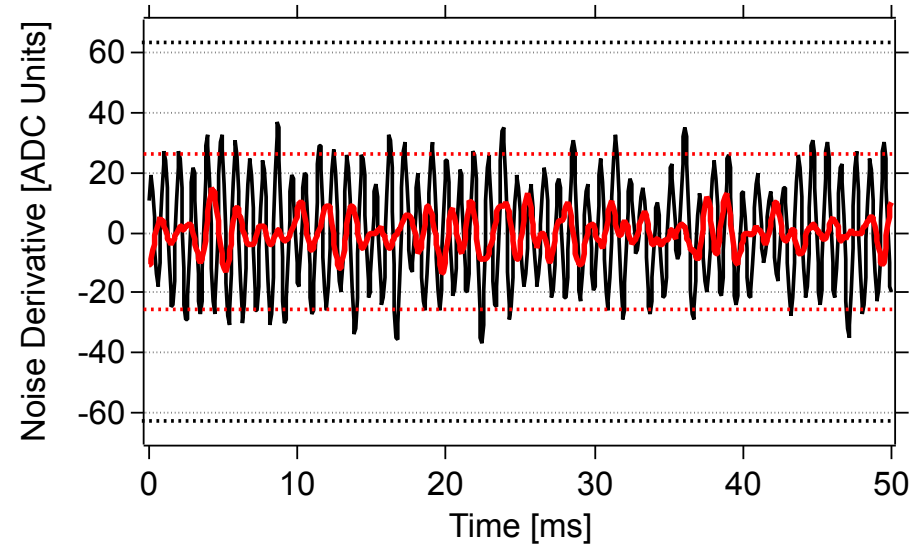
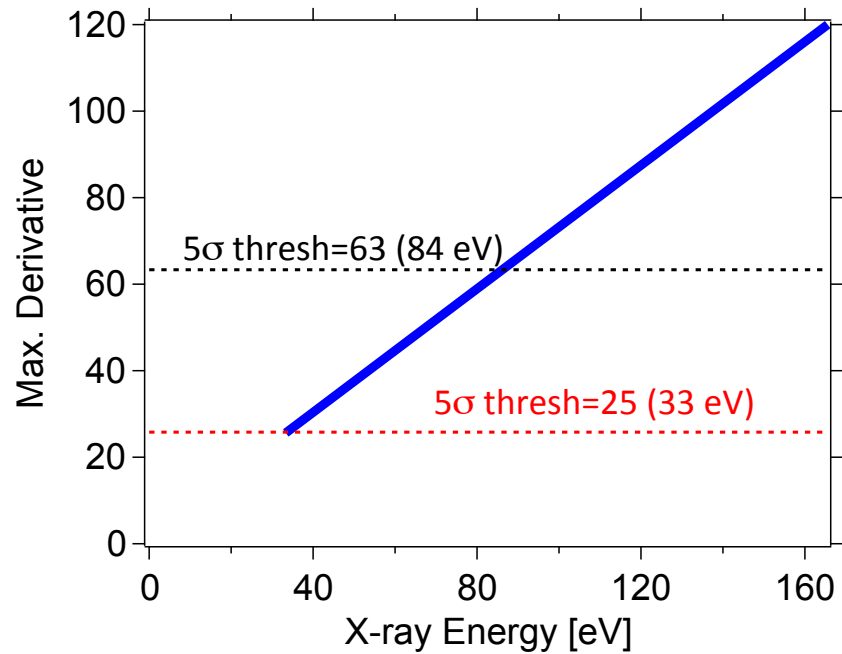
$$\Delta E \propto (T E_{max})^{0.5} \quad E_{max} \propto C T/\alpha$$

$$\Delta E = \sqrt{4k_b T^2 \frac{C}{\alpha} \sqrt{2(1+2\beta)(1+M^2)}} \quad \rightarrow \text{For our TESs}$$

β scales with α      M<sup>2</sup> depends on α  
high α (>100) → high M<sup>2</sup>

- Use matched “optimal” filter for standard event processing for best  $\Delta E$ 
  - alternative analysis approaches are in development for non-linear devices and high count-rate applications

# Energy Threshold (example, using $\Delta E_{FWHM} \sim 4$ eV silicon thermistor SXS array)



High-frequency noise can have large effect on trigger threshold, but little impact on energy resolution.

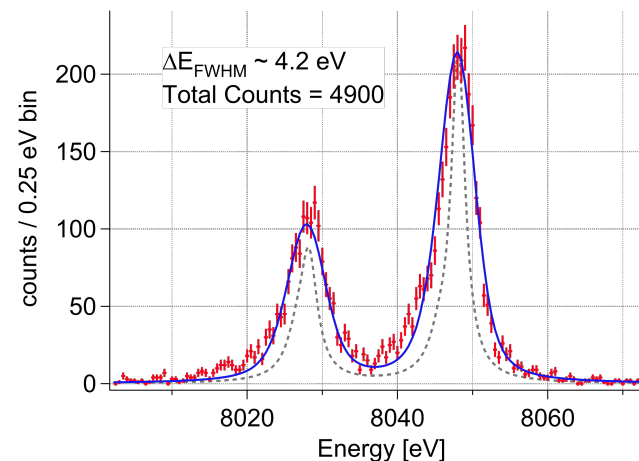
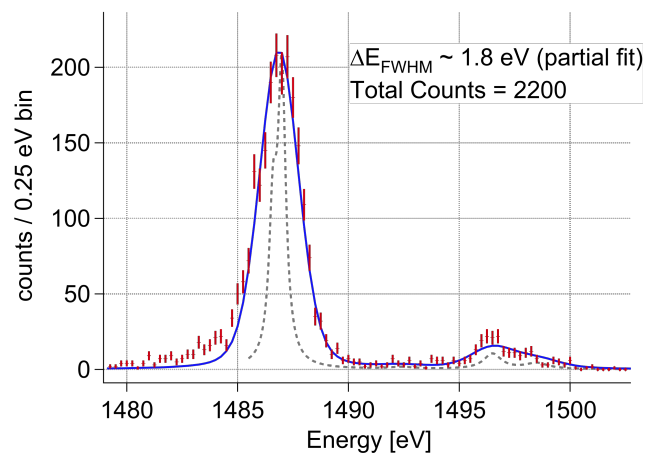
Low instrument collecting area at low energy so not a driving requirement; we trigger as low as possible to reduce background and avoid contamination/pile-up.

# Technical Challenges (1)

## Thermalization

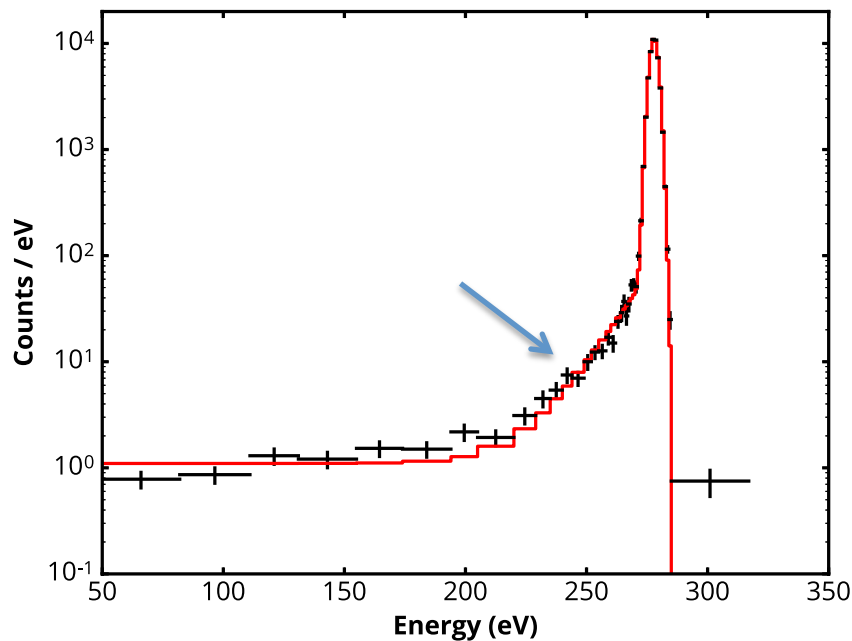
## Insufficient thermalization can lead to degraded resolution and/or distorted line shape.

- want rapid energy downconversion following photon absorption, where device thermalization is complete prior to sensor response (measuring a single  $\Delta T$ )
- If thermalization is not rapid or complete or there are other energy loss mechanisms, signal size can depend on absorption position, degrading resolution and distorting line shape
  - silicon thermistor devices: use separate absorber to avoid absorbing in Si, controlled/reproducible absorber attachment process
  - TES devices: use separate absorber; Au layer in absorbers for thermalization, electroplated Bi for stopping power
  - solid substrate TES devices (no membrane isolation): make absorber attachment stems w/ small area to minimize athermal phonon loss to substrate

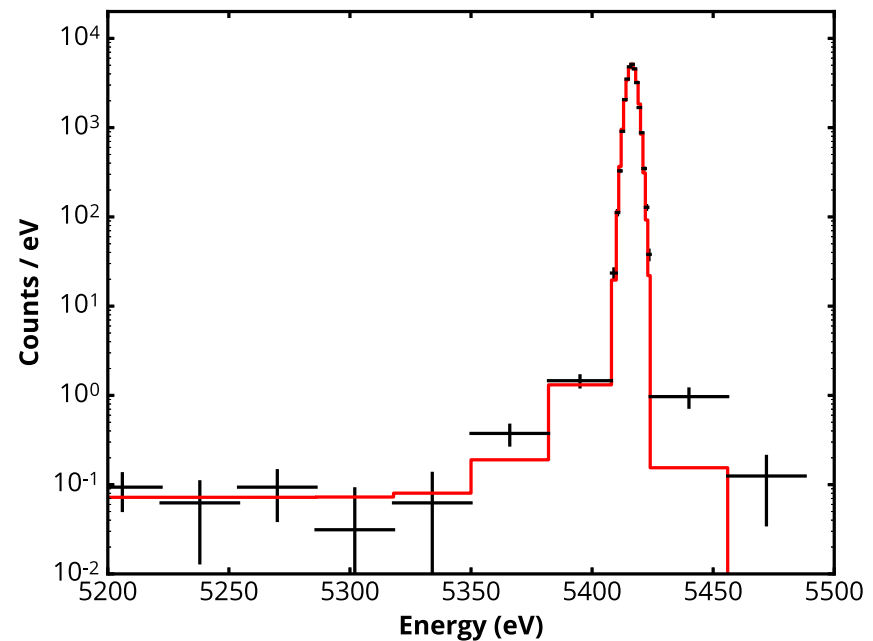


## Example of Surface Effects (energy loss)

- Small exponential tail related to photons absorbed near surface of HgTe absorbers (Astro-H SXS detectors)



~2% at 270 eV



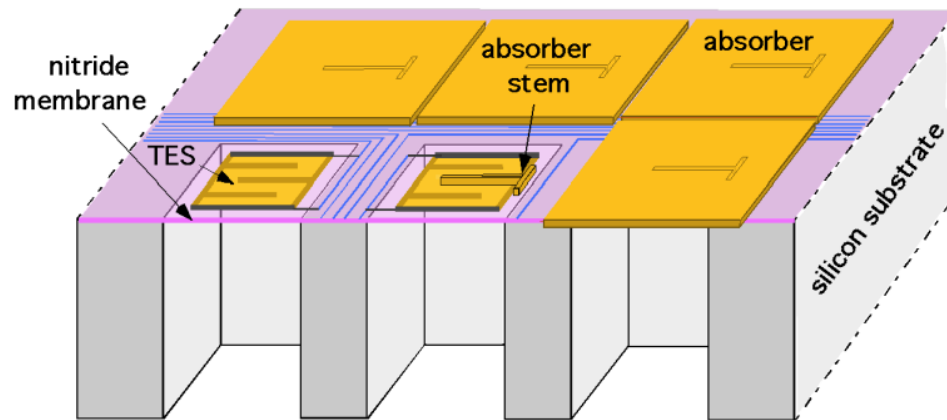
<0.1% at 5410 eV

- Tail measured from 0.3 keV – 8 keV. Fraction of counts in tail drops with energy in manner consistent with decreasing fraction of photons absorbed near surface.
- Possible trapping states due to altered band structure near surface (first tens of Å)?

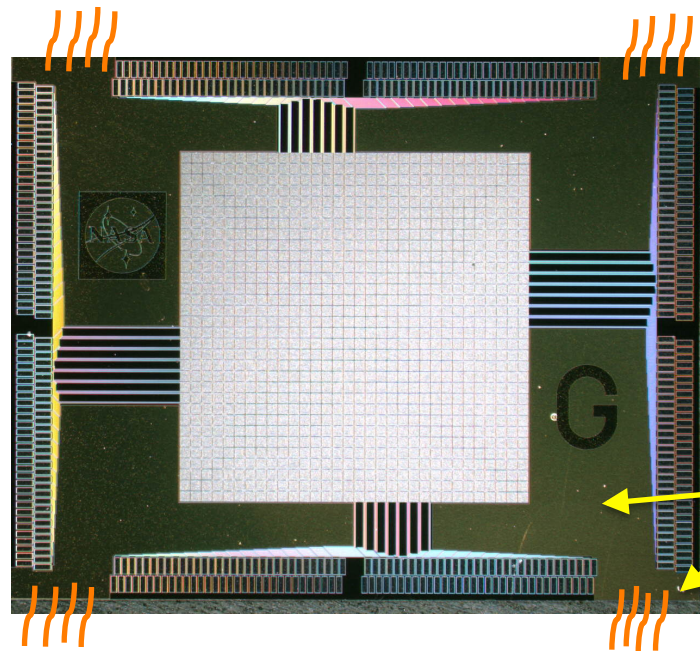
# Technical Challenges (2)

## Heatsinking

# Heatsinking



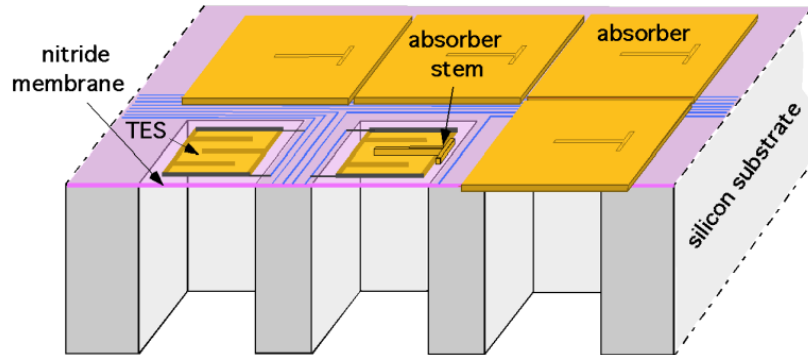
- 1) Effective  $T_b$  change caused by TES bias power
- 2) pixel-to-pixel crosstalk  
– need good heatsinking to accommodate high x-ray fluxes



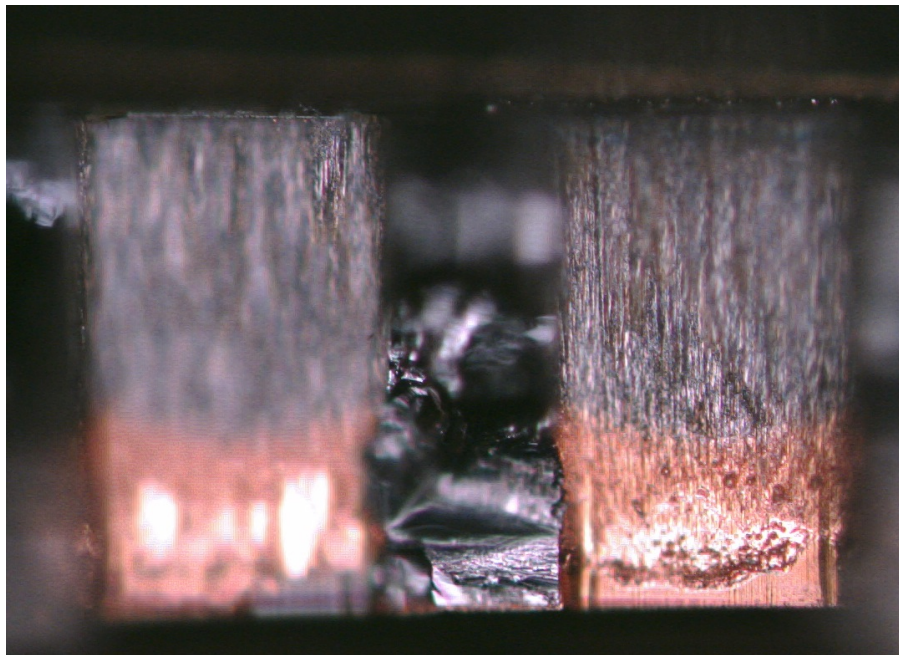
thick Au layer  
connect to heat sink with Au bonds



## Improve heatsinking: Coat sidewalls of wells with thick Cu



- steep angle deposition from back
- rotating jig to deposit on all four sidewalls
- remove DRIE passivant before deposition to ensure good Si/Cu conductance



300 μm  
130 μm

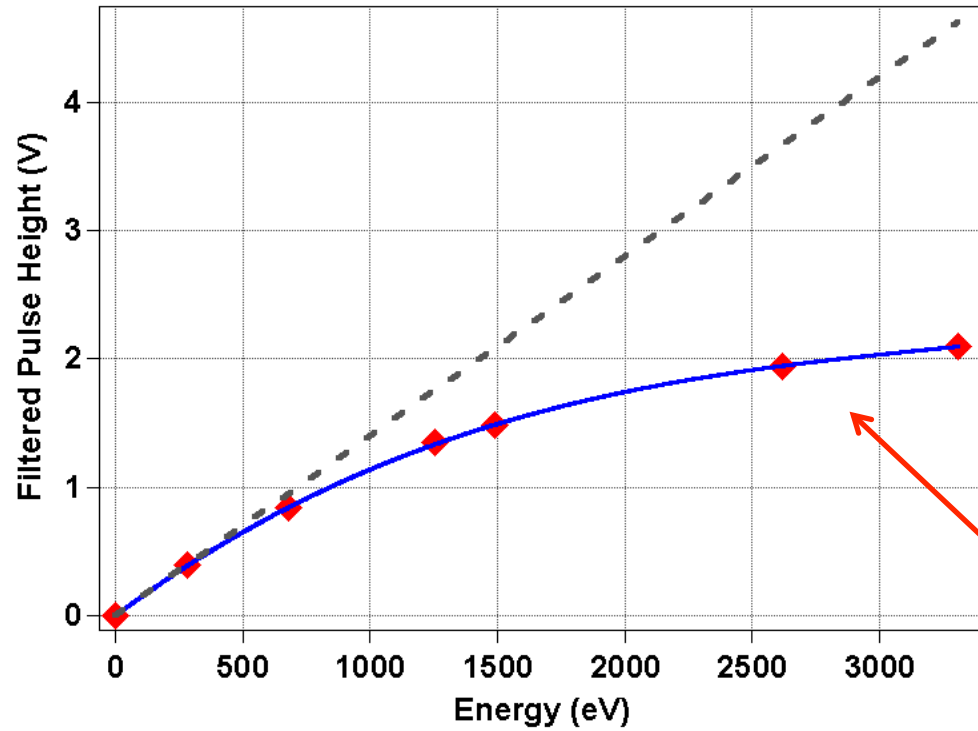


40% coating of sidewalls on this wafer (80% currently possible)  
3.5 micron thick

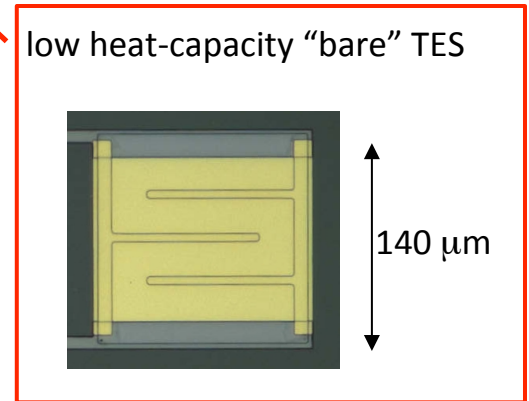
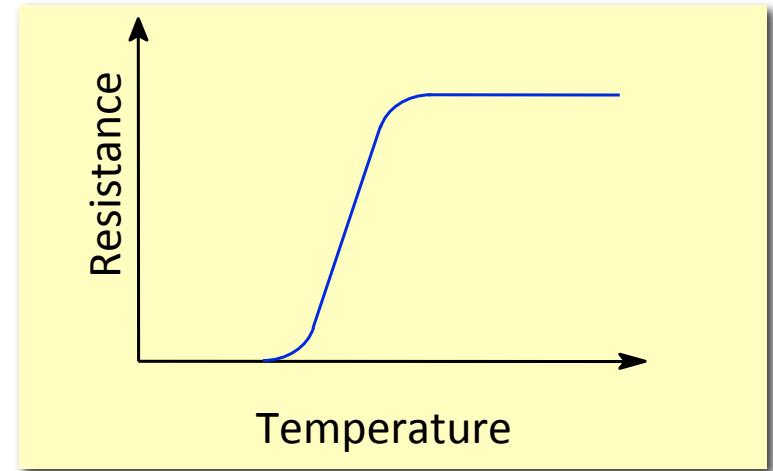
# Reduced Heat Capacity Devices (1)

## X-ray TES Microcalorimeters

# Typical low-C response in soft X-ray band:

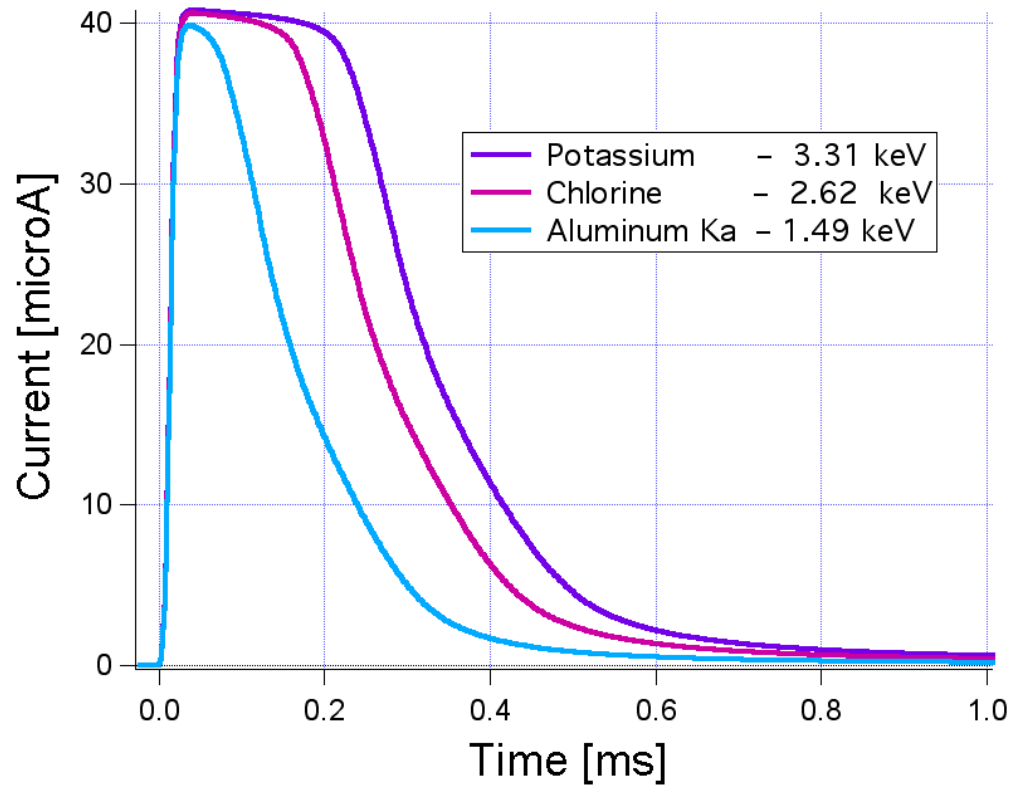


Heat capacity  $C \sim 0.1$  pJ/K (x10 smaller than standard design)

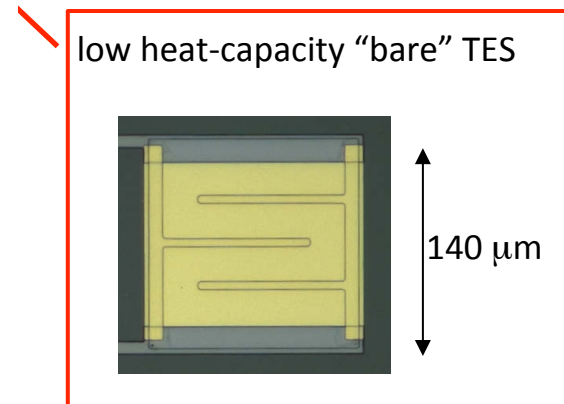
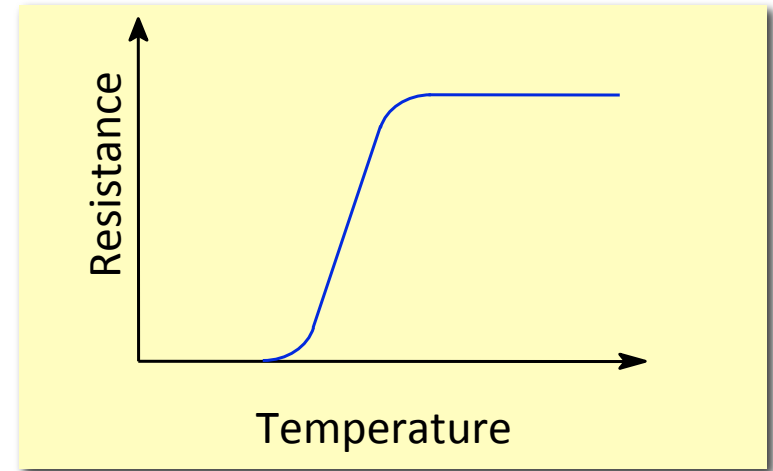


$$\Delta E \propto T C^{0.5}$$

## Typical low-C response in soft X-ray band:

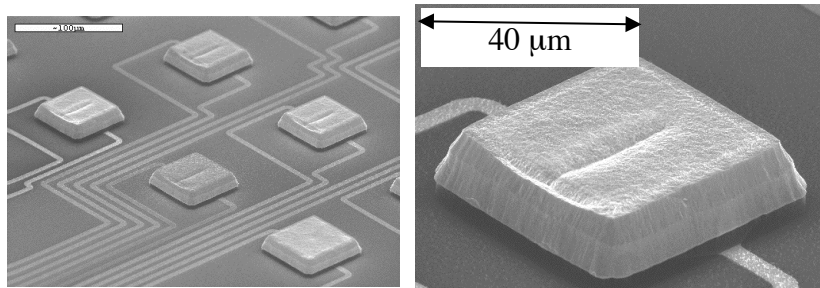
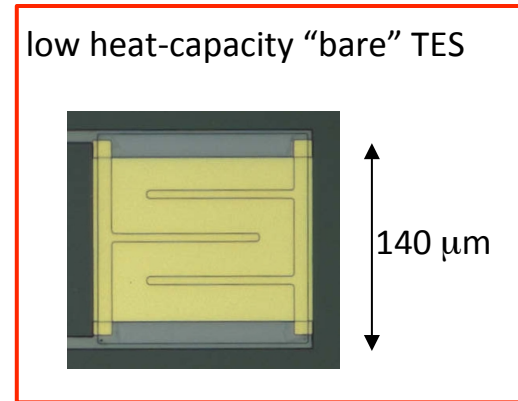
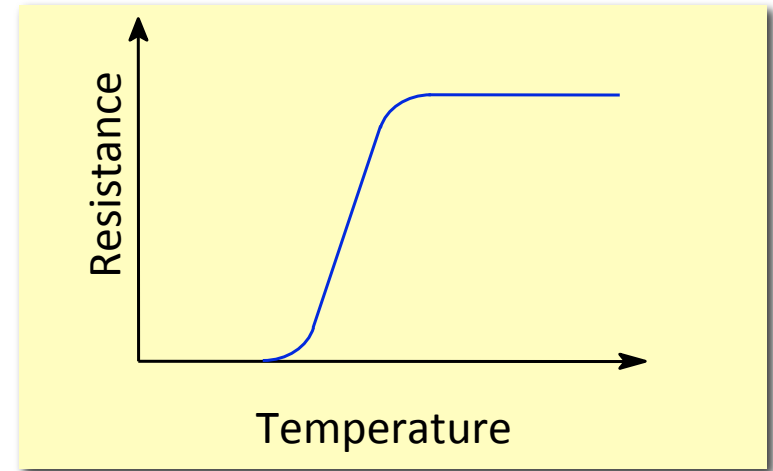
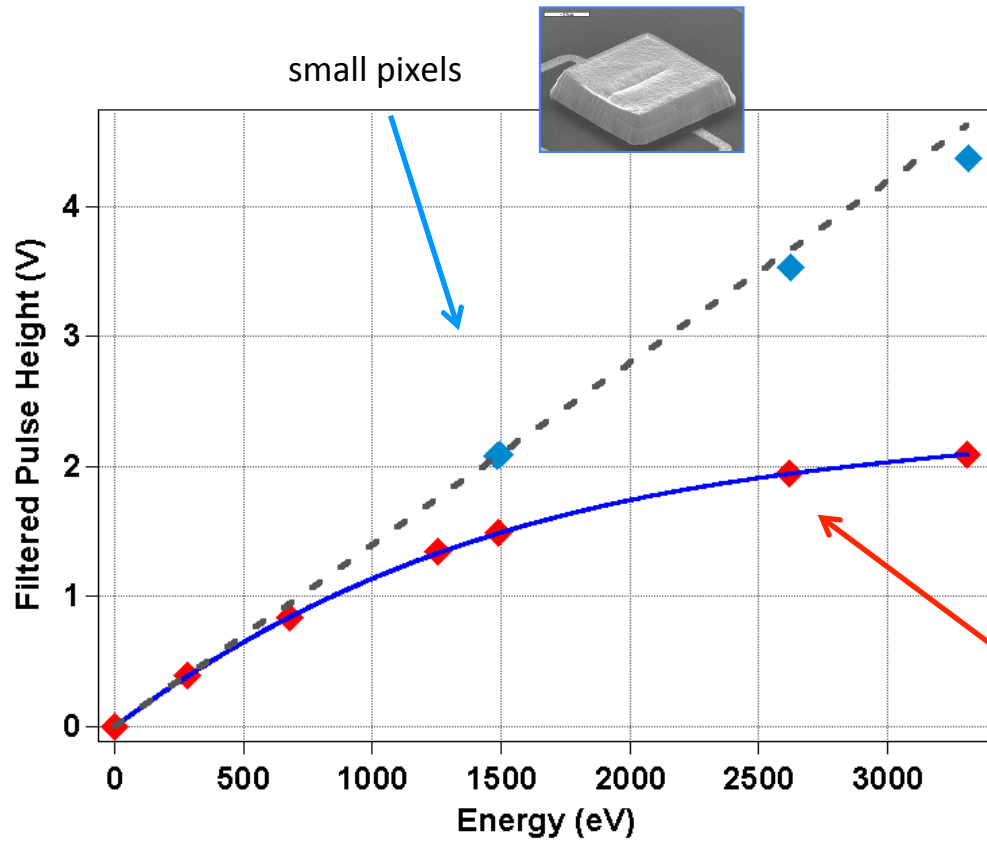


Heat capacity  $C \sim 0.1 \text{ pJ/K}$  (x10 smaller than standard design)



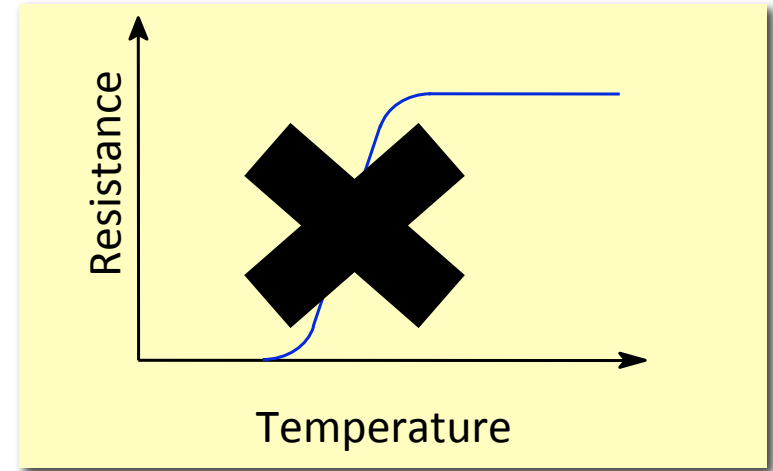
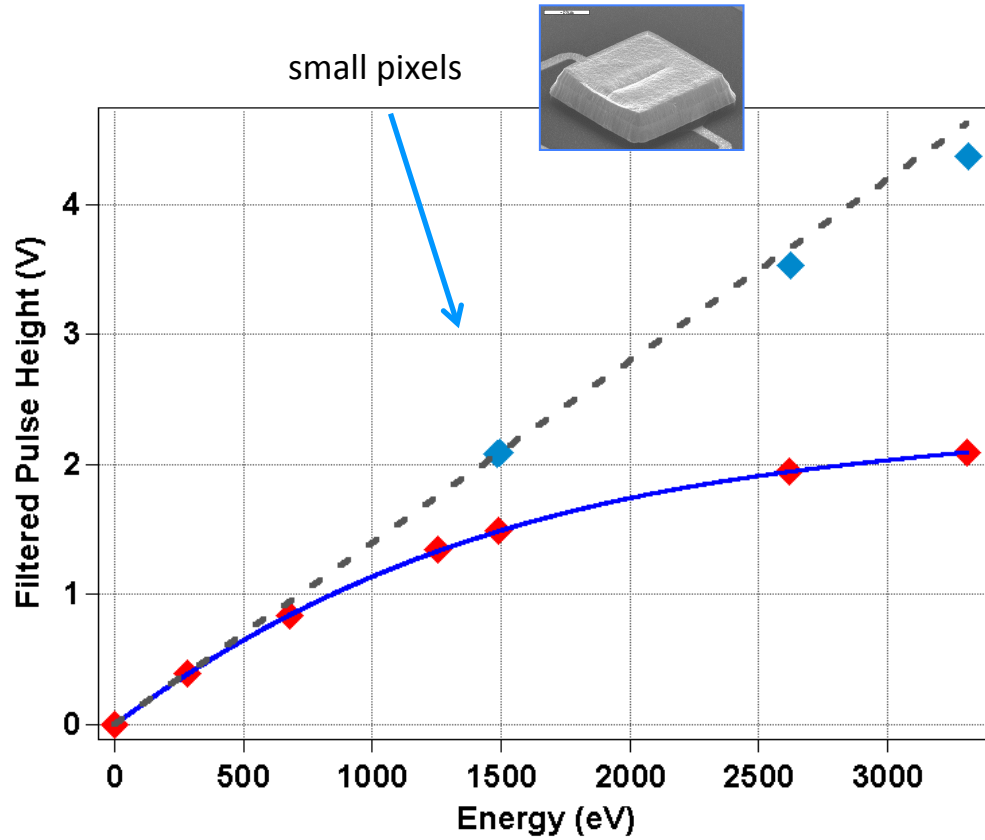
$$\Delta E \propto T C^{0.5}$$

# New operating regime for X-ray TESs – soft saturation:



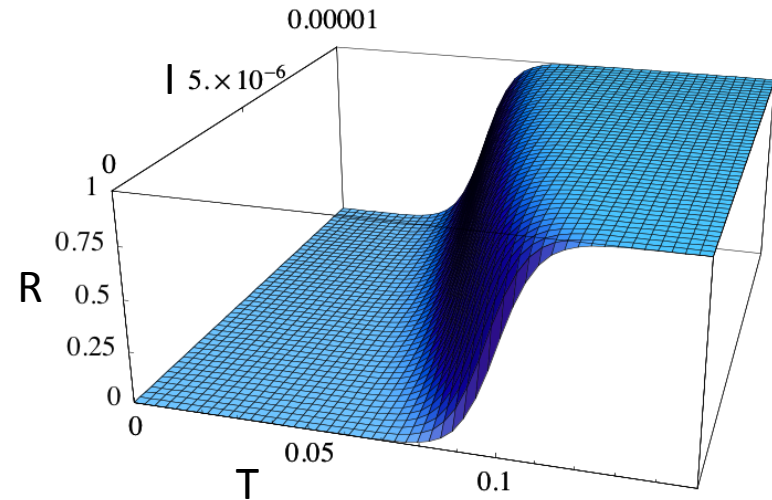
miniaturized pixel: 35 μm TES, 57 μm x 57 μm x 4.5 μm absorber

# New operating regime for X-ray TESs – soft saturation:



highly current dependent transition

enabled good energy resolution over extended energy range, and  $\Delta E_{FWHM} = 0.72 \text{ eV}$  at 1.5 keV



R-I-T Surface

# Reduced Heat Capacity Devices (2)

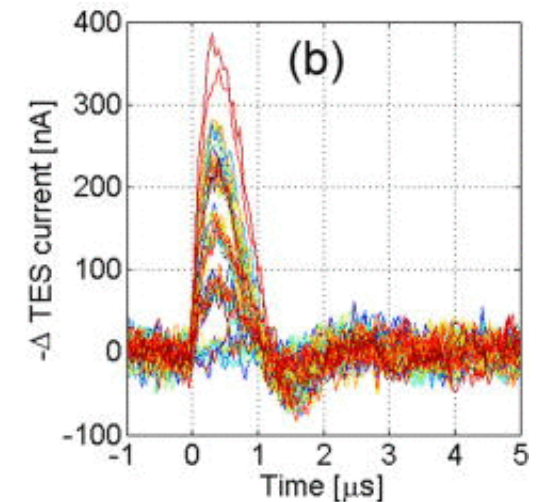
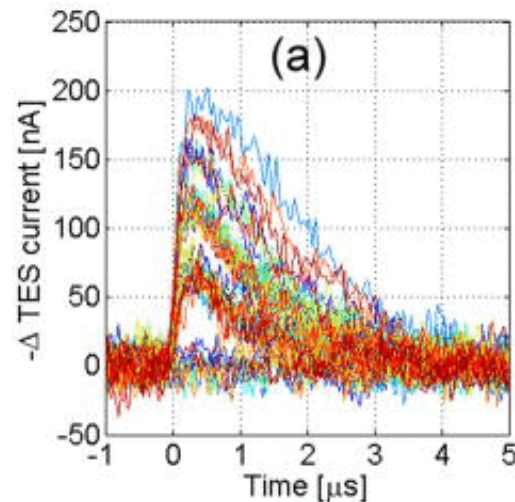
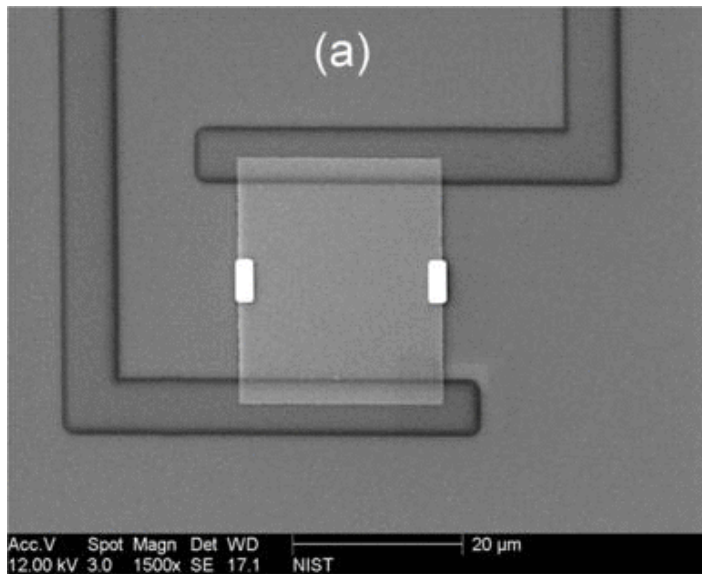
## Optical TES Microcalorimeters

# Optical TES Microcalorimeters

Stanford (Cabrera et al.), NIST/Boulder (Nam, Lita et al.)

## Example of NIST/Boulder optical devices:

- W-TES with Al leads (also explored Hf-TES)
- device  $T_c$  tuned to  $\sim 150\text{mK}$
- $25 \times 25 \mu\text{m}^2$
- Detecting photons of  $0.6 \text{ eV}$  ( $2 \mu\text{m}$ ) –  $3 \text{ eV}$  ( $400 \text{ nm}$ )
- push to get high QE, low timing jitter, faster decay times

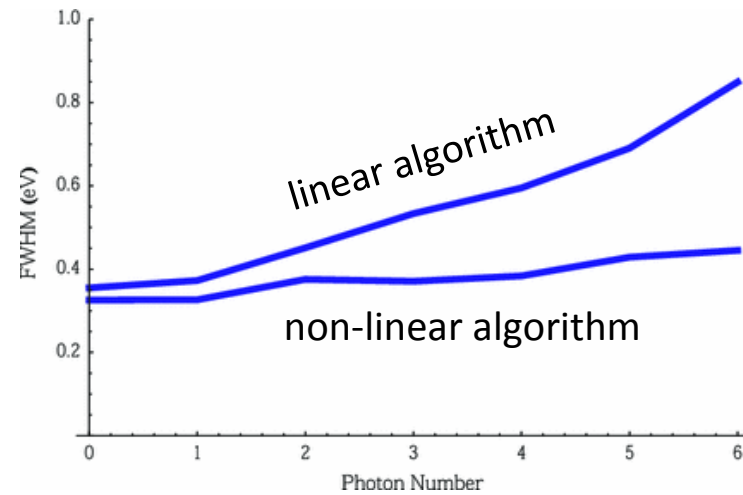
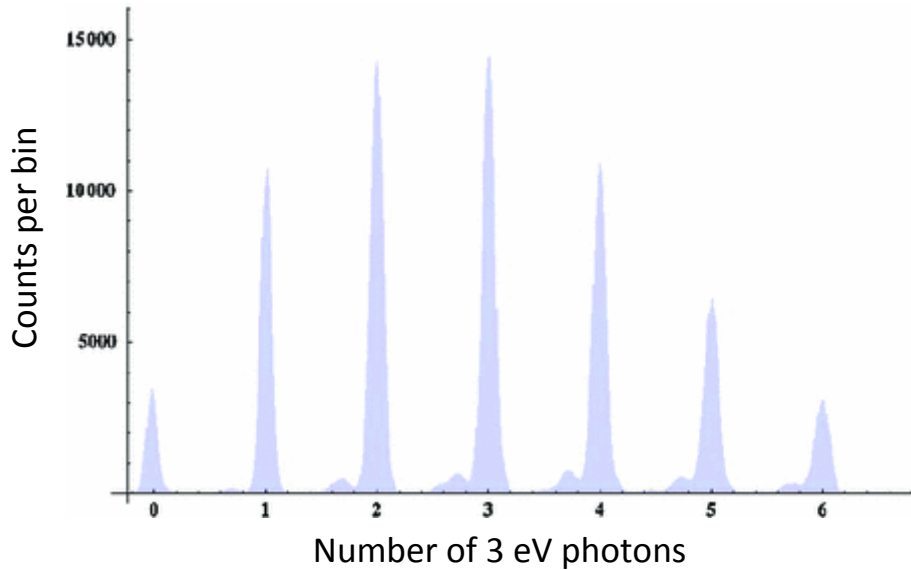
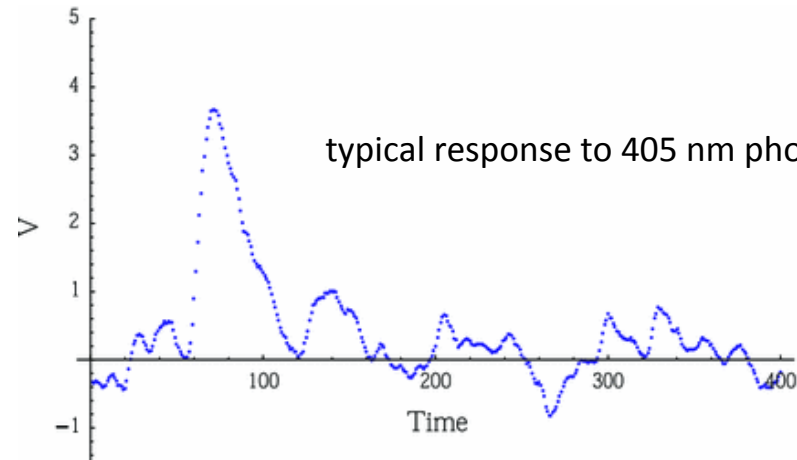
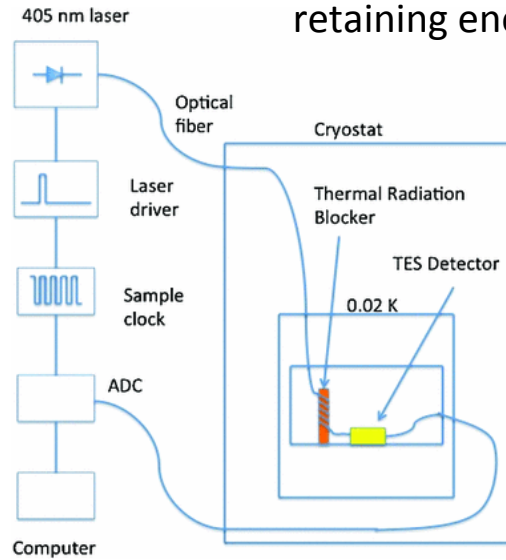


B. Calkins, A. Lita, A. Fox, and S. W. Nam. *APL* (2011).



# Optical TES Microcalorimeters – with advanced pulse processing

retaining energy resolving power beyond linear range



## Lower energy optimization thoughts:

### smaller C:

how: smaller device volume, different materials

cautions: often means smaller collecting area; in case of smaller TESs, proximity from leads can raise  $T_c$  and change transition shape

### lower operating T:

how: can tune sensor operating temperature – bilayer thicknesses (Mo/Au, Mo/Cu) or crystal structure (W)

cautions: only gain like  $\sqrt{T}$ , requires lower heatsink temperature

### increase $\alpha$ :

how: not straightforward, change normal metal features on TESs, ...

cautions: we observe excess noise ( $M^2$  term) with high  $\alpha$

advanced pulse processing techniques: retain device performance into saturated regime

cautions: calibration needs increase significantly